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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	133
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p125-pq208

The absolute maximum junction temperature is 100°C. EQ 1 shows a sample calculation of the absolute maximum power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja} (\text{°C/W})} = \frac{100^{\circ}\text{C} - 70^{\circ}\text{C}}{20.5^{\circ}\text{C/W}} = 1.463 \text{ W}$$

EQ 1

Table 2-5 • Package Thermal Resistivities

Package Type	Device	Pin Count	θ_{jc}	θ_{ja}			Units
				Still Air	200 ft/min	500 ft/min	
Quad Flat No Lead	A3P030	132	0.4	21.4	16.8	15.3	°C/W
	A3P060	132	0.3	21.2	16.6	15.0	°C/W
	A3P125	132	0.2	21.1	16.5	14.9	°C/W
	A3P250	132	0.1	21.0	16.4	14.8	°C/W
Very Thin Quad Flat Pack (VQFP)	All devices	100	10.0	35.3	29.4	27.1	°C/W
Thin Quad Flat Pack (TQFP)	All devices	144	11.0	33.5	28.0	25.7	°C/W
Plastic Quad Flat Pack (PQFP)	All devices	208	8.0	26.1	22.5	20.8	°C/W
Fine Pitch Ball Grid Array (FBGA)	See note*	144	3.8	26.9	22.9	21.5	°C/W
	See note*	256	3.8	26.6	22.8	21.5	°C/W
	See note*	484	3.2	20.5	17.0	15.9	°C/W
	A3P1000	144	6.3	31.6	26.2	24.2	°C/W
	A3P1000	256	6.6	28.1	24.4	22.7	°C/W
	A3P1000	484	8.0	23.3	19.0	16.7	°C/W

Note: *This information applies to all ProASIC3 devices except the A3P1000. Detailed device/package thermal information will be available in future revisions of the datasheet.

Temperature and Voltage Derating Factors

Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays
 (normalized to $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425 \text{ V}$)

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.88	0.93	0.95	1.00	1.02	1.04
1.500	0.83	0.88	0.90	0.95	0.96	0.98
1.575	0.80	0.84	0.87	0.91	0.93	0.94

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

P_{AC1} , P_{AC2} , P_{AC3} , and P_{AC4} are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-16 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution— $P_{OUTPUTS}$

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-16 on page 2-14](#).

β_1 is the I/O buffer enable rate—guidelines are provided in [Table 2-17 on page 2-14](#).

F_{CLK} is the global clock signal frequency.

Table 2-29 • I/O Output Buffer Maximum Resistances¹
Applicable to Standard Plus I/O Banks

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range ⁴	100 μA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / IOL_{spec}$
3. $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / IOH_{spec}$
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

Timing Characteristics

Table 2-60 • 2.5 V LVC MOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	8.66	0.04	1.31	0.43	7.83	8.66	2.68	2.30	10.07	10.90	ns
	–1	0.51	7.37	0.04	1.11	0.36	6.66	7.37	2.28	1.96	8.56	9.27	ns
	–2	0.45	6.47	0.03	0.98	0.32	5.85	6.47	2.00	1.72	7.52	8.14	ns
6 mA	Std.	0.60	5.17	0.04	1.31	0.43	5.04	5.17	3.05	3.00	7.27	7.40	ns
	–1	0.51	4.39	0.04	1.11	0.36	4.28	4.39	2.59	2.55	6.19	6.30	ns
	–2	0.45	3.86	0.03	0.98	0.32	3.76	3.86	2.28	2.24	5.43	5.53	ns
8 mA	Std.	0.60	5.17	0.04	1.31	0.43	5.04	5.17	3.05	3.00	7.27	7.40	ns
	–1	0.51	4.39	0.04	1.11	0.36	4.28	4.39	2.59	2.55	6.19	6.30	ns
	–2	0.45	3.86	0.03	0.98	0.32	3.76	3.86	2.28	2.24	5.43	5.53	ns
12 mA	Std.	0.60	3.56	0.04	1.31	0.43	3.63	3.43	3.30	3.44	5.86	5.67	ns
	–1	0.51	3.03	0.04	1.11	0.36	3.08	2.92	2.81	2.92	4.99	4.82	ns
	–2	0.45	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
16 mA	Std.	0.60	3.35	0.04	1.31	0.43	3.41	3.06	3.36	3.55	5.65	5.30	ns
	–1	0.51	2.85	0.04	1.11	0.36	2.90	2.60	2.86	3.02	4.81	4.51	ns
	–2	0.45	2.50	0.03	0.98	0.32	2.55	2.29	2.51	2.65	4.22	3.96	ns
24 mA	Std.	0.60	3.09	0.04	1.31	0.43	3.15	2.44	3.44	4.00	5.38	4.68	ns
	–1	0.51	2.63	0.04	1.11	0.36	2.68	2.08	2.92	3.40	4.58	3.98	ns
	–2	0.45	2.31	0.03	0.98	0.32	2.35	1.82	2.57	2.98	4.02	3.49	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-62 • 2.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.28	0.04	1.30	0.43	7.41	8.28	2.25	2.07	9.64	10.51	ns
	–1	0.56	7.04	0.04	1.10	0.36	6.30	7.04	1.92	1.76	8.20	8.94	ns
	–2	0.49	6.18	0.03	0.97	0.32	5.53	6.18	1.68	1.55	7.20	7.85	ns
6 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
8 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
12 mA	Std.	0.66	3.21	0.04	1.30	0.43	3.27	3.14	2.82	3.11	5.50	5.38	ns
	–1	0.56	2.73	0.04	1.10	0.36	2.78	2.67	2.40	2.65	4.68	4.57	ns
	–2	0.49	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-63 • 2.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	10.84	0.04	1.30	0.43	10.64	10.84	2.26	1.99	12.87	13.08	ns
	–1	0.56	9.22	0.04	1.10	0.36	9.05	9.22	1.92	1.69	10.95	11.12	ns
	–2	0.49	8.10	0.03	0.97	0.32	7.94	8.10	1.68	1.49	9.61	9.77	ns
6 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
8 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
12 mA	Std.	0.66	5.63	0.04	1.30	0.43	5.73	5.51	2.83	3.01	7.97	7.74	ns
	–1	0.56	4.79	0.04	1.10	0.36	4.88	4.68	2.41	2.56	6.78	6.59	ns
	–2	0.49	4.20	0.03	0.97	0.32	4.28	4.11	2.11	2.25	5.95	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-64 • 2.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
 Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	8.20	0.04	1.29	0.43	7.24	8.20	2.03	1.91	ns
	–1	0.56	6.98	0.04	1.10	0.36	6.16	6.98	1.73	1.62	ns
	–2	0.49	6.13	0.03	0.96	0.32	5.41	6.13	1.52	1.43	ns
4 mA	Std.	0.66	8.20	0.04	1.29	0.43	7.24	8.20	2.03	1.91	ns
	–1	0.56	6.98	0.04	1.10	0.36	6.16	6.98	1.73	1.62	ns
	–2	0.49	6.13	0.03	0.96	0.32	5.41	6.13	1.52	1.43	ns
6 mA	Std.	0.66	4.77	0.04	1.29	0.43	4.55	4.77	2.38	2.55	ns
	–1	0.56	4.05	0.04	1.10	0.36	3.87	4.05	2.03	2.17	ns
	–2	0.49	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns
8 mA	Std.	0.66	4.77	0.04	1.29	0.43	4.55	4.77	2.38	2.55	ns
	–1	0.56	4.05	0.04	1.10	0.36	3.87	4.05	2.03	2.17	ns
	–2	0.49	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-65 • 2.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
 Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	–1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	–2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
4 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	–1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	–2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
6 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	–1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	–2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns
8 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	–1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	–2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-93 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-94 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)
1.64	1.94	Cross point

Note: *Measuring point = V_{trip} . See [Table 2-22 on page 2-22](#) for a complete table of trip points.

Timing Characteristics

Table 2-95 • LVPECL

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.66	1.80	0.04	1.40	ns
–1	0.56	1.53	0.04	1.19	ns
–2	0.49	1.34	0.03	1.05	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-97 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-16 on page 2-71 for more information.

Timing Characteristics

Table 2-100 • Output Enable Register Propagation Delays
 Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.59	0.67	0.79	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.31	0.36	0.42	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.44	0.50	0.58	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWPPE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.36	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Embedded SRAM and FIFO Characteristics

SRAM

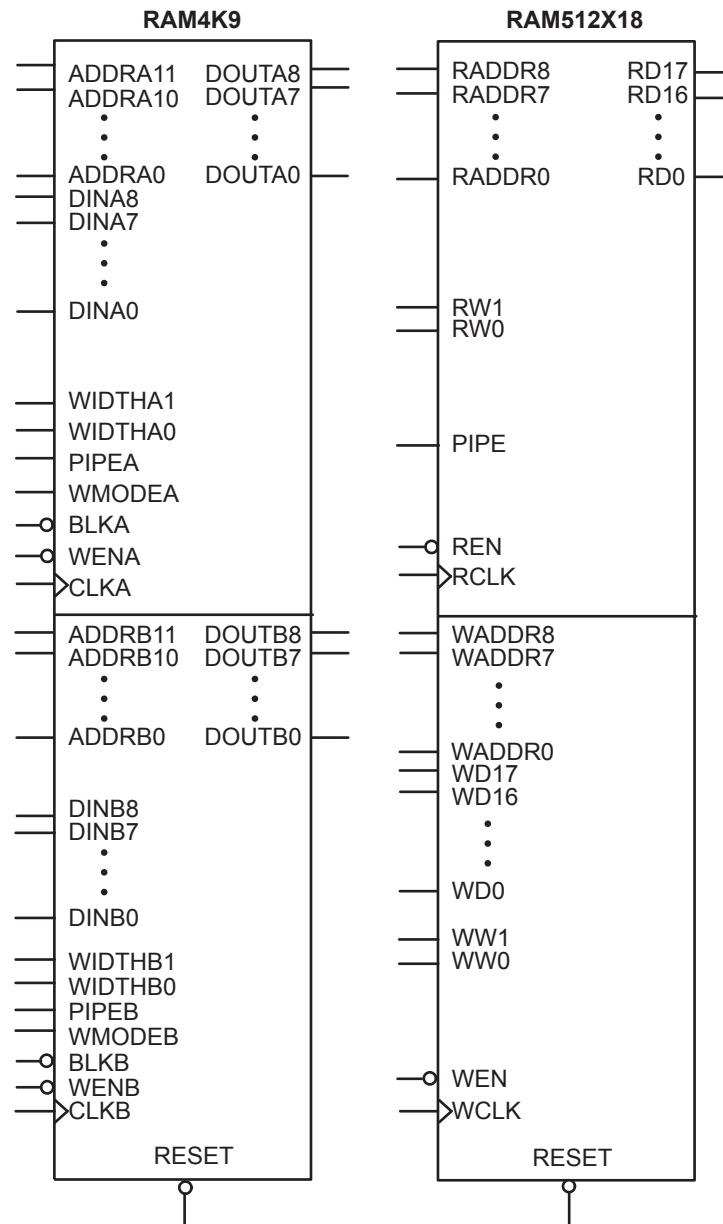


Figure 2-30 • RAM Models

Timing Waveforms

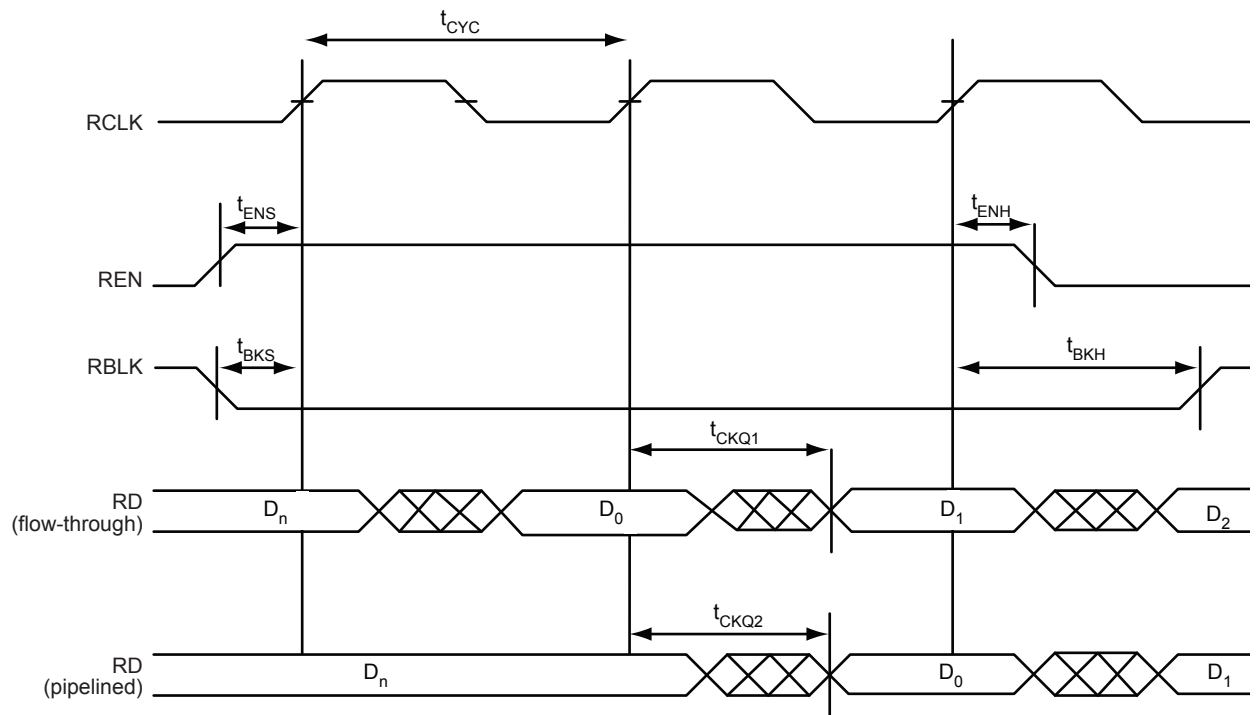


Figure 2-37 • FIFO Read

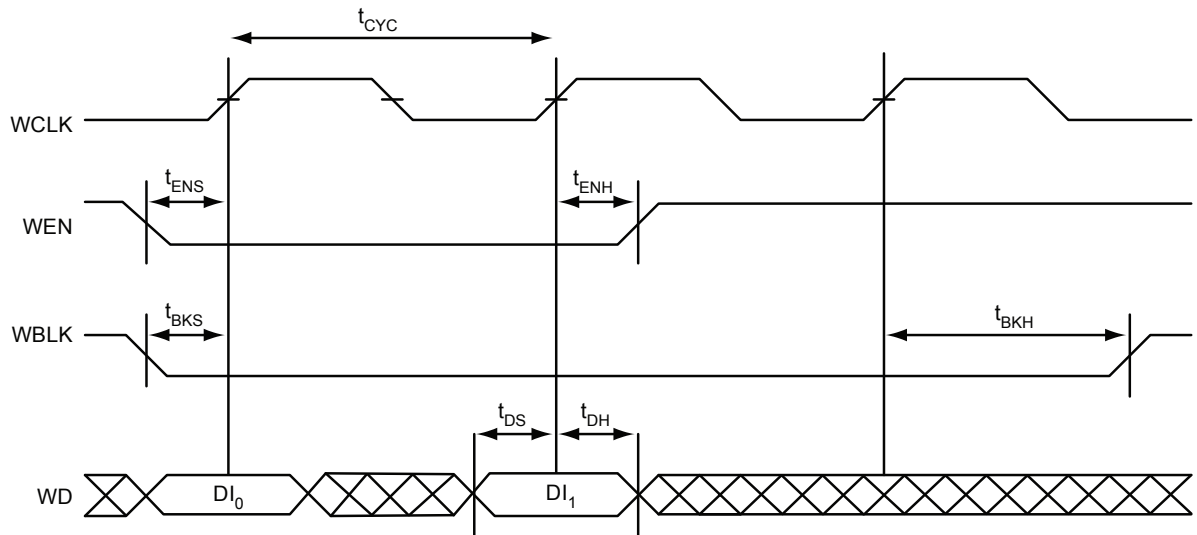


Figure 2-38 • FIFO Write

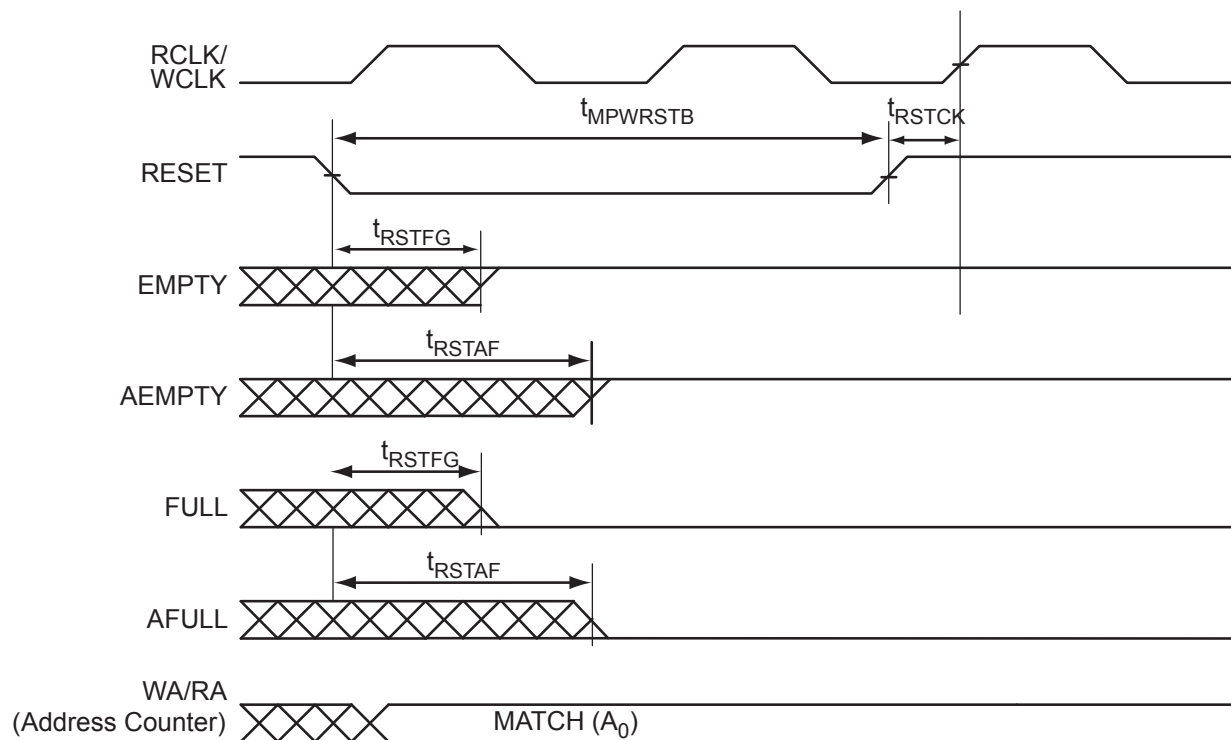


Figure 2-39 • FIFO Reset

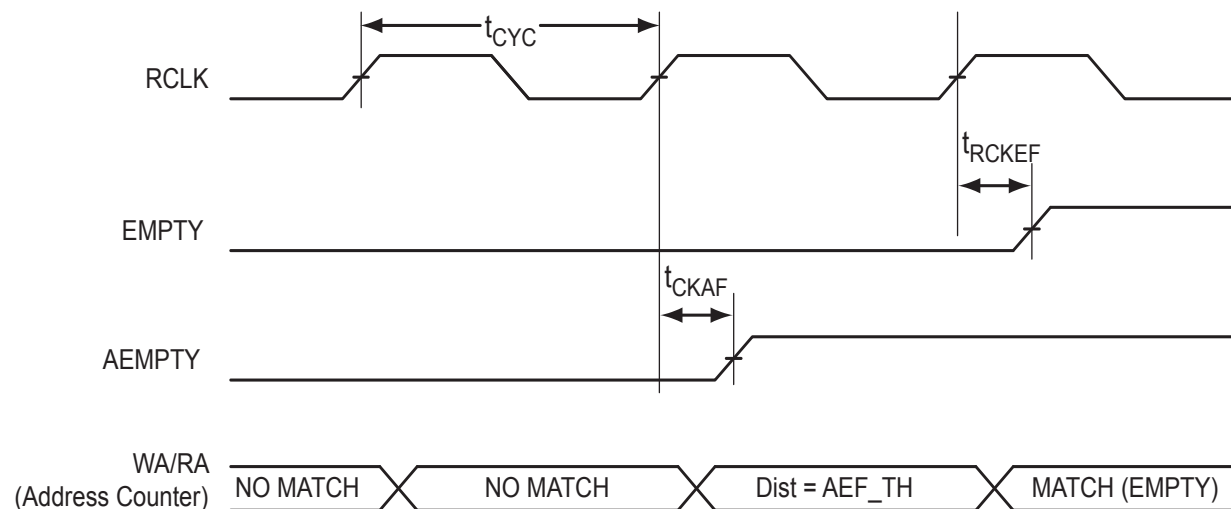


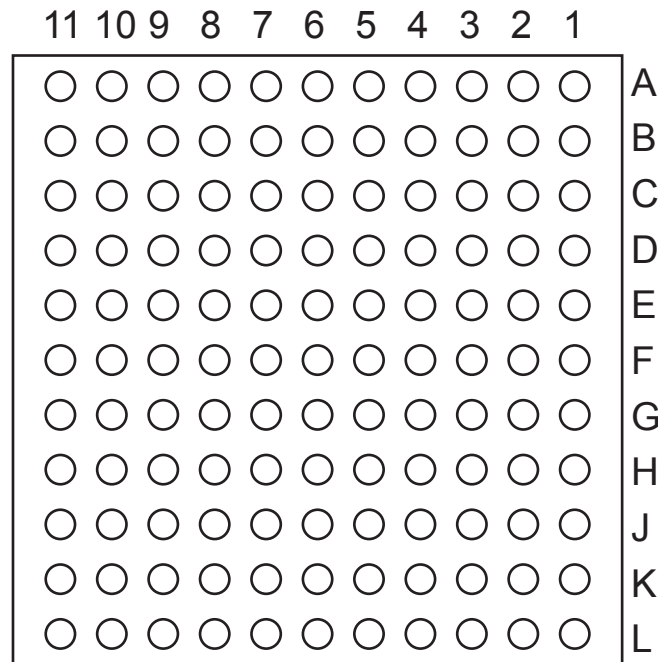
Figure 2-40 • FIFO EMPTY Flag and AEMPTY Flag Assertion

QN132	
Pin Number	A3P030 Function
A1	IO01RSB1
A2	IO81RSB1
A3	NC
A4	IO80RSB1
A5	GEC0/IO77RSB1
A6	NC
A7	GEB0/IO75RSB1
A8	IO73RSB1
A9	NC
A10	VCC
A11	IO71RSB1
A12	IO68RSB1
A13	IO63RSB1
A14	IO60RSB1
A15	NC
A16	IO59RSB1
A17	IO57RSB1
A18	VCC
A19	IO54RSB1
A20	IO52RSB1
A21	IO49RSB1
A22	IO48RSB1
A23	IO47RSB1
A24	TDI
A25	TRST
A26	IO44RSB0
A27	NC
A28	IO43RSB0
A29	IO42RSB0
A30	IO40RSB0
A31	IO39RSB0
A32	GDC0/IO36RSB0
A33	NC
A34	VCC
A35	IO34RSB0
A36	IO31RSB0

QN132	
Pin Number	A3P030 Function
A37	IO26RSB0
A38	IO23RSB0
A39	NC
A40	IO22RSB0
A41	IO20RSB0
A42	IO18RSB0
A43	VCC
A44	IO15RSB0
A45	IO12RSB0
A46	IO10RSB0
A47	IO09RSB0
A48	IO06RSB0
B1	IO02RSB1
B2	IO82RSB1
B3	GND
B4	IO79RSB1
B5	NC
B6	GND
B7	IO74RSB1
B8	NC
B9	GND
B10	IO70RSB1
B11	IO67RSB1
B12	IO64RSB1
B13	IO61RSB1
B14	GND
B15	IO58RSB1
B16	IO56RSB1
B17	GND
B18	IO53RSB1
B19	IO50RSB1
B20	GND
B21	IO46RSB1
B22	TMS
B23	TDO
B24	IO45RSB0

QN132	
Pin Number	A3P030 Function
B25	GND
B26	NC
B27	IO41RSB0
B28	GND
B29	GDA0/IO37RSB0
B30	NC
B31	GND
B32	IO33RSB0
B33	IO30RSB0
B34	IO27RSB0
B35	IO24RSB0
B36	GND
B37	IO21RSB0
B38	IO19RSB0
B39	GND
B40	IO16RSB0
B41	IO13RSB0
B42	GND
B43	IO08RSB0
B44	IO05RSB0
C1	IO03RSB1
C2	IO00RSB1
C3	NC
C4	IO78RSB1
C5	GEA0/IO76RSB1
C6	NC
C7	NC
C8	VCCIB1
C9	IO69RSB1
C10	IO66RSB1
C11	IO65RSB1
C12	IO62RSB1
C13	NC
C14	NC
C15	IO55RSB1
C16	VCCIB1

CS121 – Bottom View



Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

PQ208	
Pin Number	A3P250 Function
109	TRST
110	VJTAG
111	GDA0/IO60VDB1
112	GDA1/IO60UDB1
113	GDB0/IO59VDB1
114	GDB1/IO59UDB1
115	GDC0/IO58VDB1
116	GDC1/IO58UDB1
117	IO57VDB1
118	IO57UDB1
119	IO56NDB1
120	IO56PDB1
121	IO55RSB1
122	GND
123	VCCIB1
124	NC
125	NC
126	VCC
127	IO53NDB1
128	GCC2/IO53PDB1
129	GCB2/IO52PSB1
130	GND
131	GCA2/IO51PSB1
132	GCA1/IO50PDB1
133	GCA0/IO50NDB1
134	GCB0/IO49NDB1
135	GCB1/IO49PDB1
136	GCC0/IO48NDB1
137	GCC1/IO48PDB1
138	IO47NDB1
139	IO47PDB1
140	VCCIB1
141	GND
142	VCC
143	IO46RSB1
144	IO45NDB1

PQ208	
Pin Number	A3P250 Function
145	IO45PDB1
146	IO44NDB1
147	IO44PDB1
148	IO43NDB1
149	GBC2/IO43PDB1
150	IO42NDB1
151	GBB2/IO42PDB1
152	IO41NDB1
153	GBA2/IO41PDB1
154	VMV1
155	GNDQ
156	GND
157	NC
158	GBA1/IO40RSB0
159	GBA0/IO39RSB0
160	GBB1/IO38RSB0
161	GBB0/IO37RSB0
162	GND
163	GBC1/IO36RSB0
164	GBC0/IO35RSB0
165	IO34RSB0
166	IO33RSB0
167	IO32RSB0
168	IO31RSB0
169	IO30RSB0
170	VCCIB0
171	VCC
172	IO29RSB0
173	IO28RSB0
174	IO27RSB0
175	IO26RSB0
176	IO25RSB0
177	IO24RSB0
178	GND
179	IO23RSB0
180	IO22RSB0

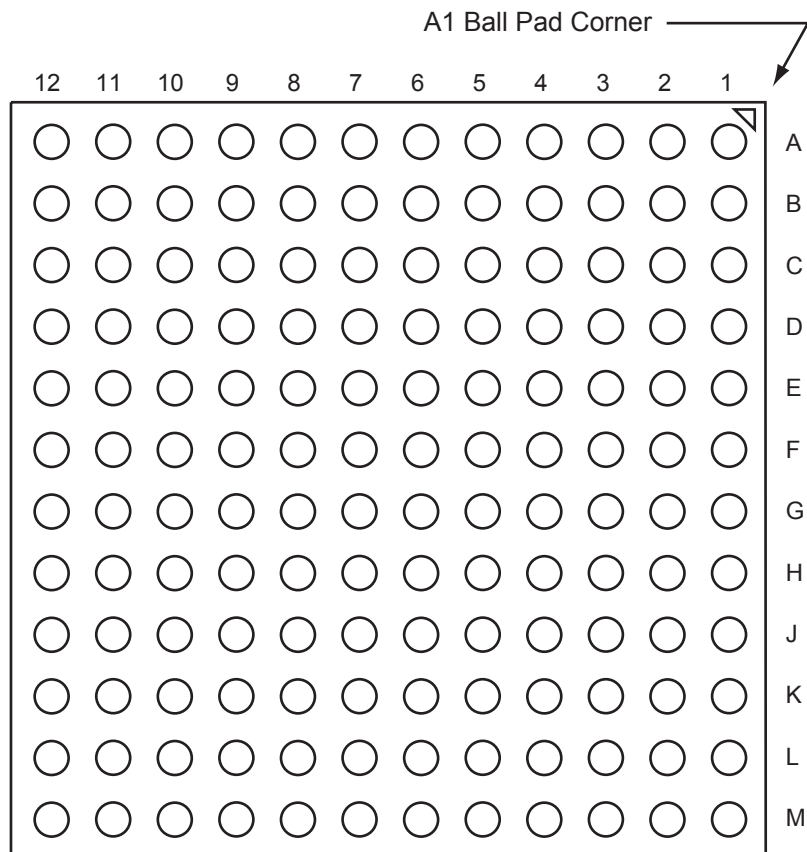
PQ208	
Pin Number	A3P250 Function
181	IO21RSB0
182	IO20RSB0
183	IO19RSB0
184	IO18RSB0
185	IO17RSB0
186	VCCIB0
187	VCC
188	IO16RSB0
189	IO15RSB0
190	IO14RSB0
191	IO13RSB0
192	IO12RSB0
193	IO11RSB0
194	IO10RSB0
195	GND
196	IO09RSB0
197	IO08RSB0
198	IO07RSB0
199	IO06RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

PQ208	
Pin Number	A3P400 Function
1	GND
2	GAA2/IO155UDB3
3	IO155VDB3
4	GAB2/IO154UDB3
5	IO154VDB3
6	GAC2/IO153UDB3
7	IO153VDB3
8	IO152UDB3
9	IO152VDB3
10	IO151UDB3
11	IO151VDB3
12	IO150PDB3
13	IO150NDB3
14	IO149PDB3
15	IO149NDB3
16	VCC
17	GND
18	VCCIB3
19	IO148PDB3
20	IO148NDB3
21	GFC1/IO147PDB3
22	GFC0/IO147NDB3
23	GFB1/IO146PDB3
24	GFB0/IO146NDB3
25	VCOMPLF
26	GFA0/IO145NPB3
27	VCCPLF
28	GFA1/IO145PPB3
29	GND
30	GFA2/IO144PDB3
31	IO144NDB3
32	GFB2/IO143PDB3
33	IO143NDB3
34	GFC2/IO142PDB3
35	IO142NDB3
36	NC

PQ208	
Pin Number	A3P400 Function
37	IO141PSB3
38	IO140PDB3
39	IO140NDB3
40	VCCIB3
41	GND
42	IO138PDB3
43	IO138NDB3
44	GEC1/IO137PDB3
45	GEC0/IO137NDB3
46	GEB1/IO136PDB3
47	GEB0/IO136NDB3
48	GEA1/IO135PDB3
49	GEA0/IO135NDB3
50	VMV3
51	GNDQ
52	GND
53	VMV2
54	NC
55	GEA2/IO134RSB2
56	GEB2/IO133RSB2
57	GEC2/IO132RSB2
58	IO131RSB2
59	IO130RSB2
60	IO129RSB2
61	IO128RSB2
62	VCCIB2
63	IO125RSB2
64	IO123RSB2
65	GND
66	IO121RSB2
67	IO119RSB2
68	IO117RSB2
69	IO115RSB2
70	IO113RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P400 Function
73	IO112RSB2
74	IO111RSB2
75	IO110RSB2
76	IO109RSB2
77	IO108RSB2
78	IO107RSB2
79	IO106RSB2
80	IO104RSB2
81	GND
82	IO102RSB2
83	IO101RSB2
84	IO100RSB2
85	IO99RSB2
86	IO98RSB2
87	IO97RSB2
88	VCC
89	VCCIB2
90	IO94RSB2
91	IO92RSB2
92	IO90RSB2
93	IO88RSB2
94	IO86RSB2
95	IO84RSB2
96	GDC2/IO82RSB2
97	GND
98	GDB2/IO81RSB2
99	GDA2/IO80RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

FG144 – Bottom View



Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

FG144	
Pin Number	A3P400 Function
K1	GEB0/IO136NDB3
K2	GEA1/IO135PDB3
K3	GEA0/IO135NDB3
K4	GEA2/IO134RSB2
K5	IO127RSB2
K6	IO121RSB2
K7	GND
K8	IO104RSB2
K9	GDC2/IO82RSB2
K10	GND
K11	GDA0/IO79VDB1
K12	GDB0/IO78VDB1
L1	GND
L2	VMV3
L3	GEB2/IO133RSB2
L4	IO128RSB2
L5	VCCIB2
L6	IO119RSB2
L7	IO114RSB2
L8	IO110RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO132RSB2
M3	IO129RSB2
M4	IO126RSB2
M5	IO124RSB2
M6	IO122RSB2
M7	IO117RSB2
M8	IO115RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	A3P600 Function
P9	IO107RSB2
P10	IO104RSB2
P11	IO97RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO88NDB1
R1	GEA1/IO144PDB3
R2	GEA0/IO144NDB3
R3	IO139RSB2
R4	GEC2/IO141RSB2
R5	IO132RSB2
R6	IO127RSB2
R7	IO121RSB2
R8	IO114RSB2
R9	IO109RSB2
R10	IO105RSB2
R11	IO98RSB2
R12	IO96RSB2
R13	GDB2/IO90RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO137RSB2
T3	GEB2/IO142RSB2
T4	IO134RSB2
T5	IO125RSB2
T6	IO123RSB2
T7	IO118RSB2
T8	IO115RSB2
T9	IO111RSB2
T10	IO106RSB2
T11	IO102RSB2
T12	GDC2/IO91RSB2

FG256	
Pin Number	A3P600 Function
T13	IO93RSB2
T14	GDA2/IO89RSB2
T15	TMS
T16	GND

Revision	Changes	Page
Advance v0.2, (continued)	Table 2-43 was updated.	2-64
	Table 2-18 was updated.	2-45
	Pin descriptions in the "JTAG Pins" section were updated.	2-51
	The "User I/O Naming Convention" section was updated.	2-48
	Table 3-7 was updated.	3-6
	The "Methodology" section was updated.	3-10
	Table 3-40 and Table 3-39 were updated.	3-33,3-32
	The A3P250 "100-Pin VQFP*" pin table was updated.	4-14
	The A3P250 "208-Pin PQFP*" pin table was updated.	4-23
	The A3P1000 "208-Pin PQFP*" pin table was updated.	4-29
	The A3P250 "144-Pin FBGA*" pin table was updated.	4-36
	The A3P1000 "144-Pin FBGA*" pin table was updated.	4-32
	The A3P250 "256-Pin FBGA*" pin table was updated.	4-45
	The A3P1000 "256-Pin FBGA*" pin table was updated.	4-54
	The A3P1000 "484-Pin FBGA*" pin table was updated.	4-68